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With the principle of "Quality Parts, Customers Priority, Honest Operation, and Considerate Service", our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip, ALPS, ROHM, Xilinx, Pulse, ON, Everlight and Freescale. Main products comprise IC, Modules, Potentiometer, IC Socket, Relay, Connector. Our parts cover such applications as commercial, industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!



Contact us

Tel: +86-755-8981 8866 Fax: +86-755-8427 6832

Email & Skype: info@chipsmall.com Web: www.chipsmall.com

Address: A1208, Overseas Decoration Building, #122 Zhenhua RD., Futian, Shenzhen, China









CSD04060-Silicon Carbide Schottky Diode

ZERO RECOVERY® RECTIFIER

 $V_{RRM} = 600 \text{ V}$

 $I_{F(AVG)} = 4 A$

Q_c = 9 nC

Marking

CSD04060

CSD04060

Features

- 600-Volt Schottky Rectifier
- Zero Reverse Recovery Current
- Zero Forward Recovery Voltage
- High-Frequency Operation
- Temperature-Independent Switching Behavior
- Extremely Fast Switching
- Positive Temperature Coefficient on V_F

Benefits

- Replace Bipolar with Unipolar Rectifiers
- Essentially No Switching Losses
- Higher Efficiency
- Reduction of Heat Sink Requirements
- Parallel Devices Without Thermal Runaway

PIN 1 O PIN 2 O-

TO-220-2

Package

TO-220-2

TO-252-2

Package

TO-252-2

Part Number

CSD04060A

CSD04060E

O CASE

Applications

- Switch Mode Power Supplies
- Power Factor Correction
 - Typical PFC P_{out}: 400W-800W
- Motor Drives
 - Typical Power : 0.5HP-2HP

Maximum Ratings

Symbol	Parameter	Value	Unit	Test Conditions	Note
V _{RRM}	Repetitive Peak Reverse Voltage	600	V		
V_{RSM}	Surge Peak Reverse Voltage	600	V		
V _{DC}	DC Blocking Voltage	600	V		
$I_{\text{F(AVG)}}$	Average Forward Current	4 7	Α	T _c =150°C T _c =125°C	
$I_{\text{F(PEAK)}}$	Peak Forward Current	10	А	T _C =125°, T _{REP} <1 mS, Duty=0.5	
\mathbf{I}_{FRM}	Repetitive Peak Forward Surge Current	17.5 12.5	А	T_c =25°C, t_p =10 ms, Half Sine Wave T_c =125°C, t_p =10 ms, Half Sine Wave	
\mathbf{I}_{FSM}	Non-Repetitive Peak Forward Surge Current	38	Α	T_c =25°C, t_p =1.5 ms, Half Sine Wave	
\mathbf{I}_{FSM}	Non-Repetitive Peak Forward Surge Current	110	А	$T_c=25$ °C, $t_p=10$ µs, Pulse	
P_{tot}	Power Dissipation	62.5 20.8	W	T _c =25°C T _c =125°C	
$T_{_{\mathtt{J}}}$, $T_{_{\mathtt{stg}}}$	Operating Junction and Storage Temperature	-55 to +175	°C		
	TO-220 Mounting Torque	1 8.8	Nm lbf-in	M3 Screw 6-32 Screw	



Electrical Characteristics

Symbol	Parameter	Тур.	Max.	Unit	Test Conditions	Note
V _F	Forward Voltage	1.5 2.0	1.8 2.4	V	$I_F = 4 \text{ A } T_J = 25^{\circ}\text{C}$ $I_F = 4 \text{ A } T_J = 175^{\circ}\text{C}$	
I _R	Reverse Current	25 50	200 1000	μΑ	$V_R = 600 \text{ V } T_J = 25^{\circ}\text{C}$ $V_R = 600 \text{ V } T_J = 175^{\circ}\text{C}$	
Q _c	Total Capacitive Charge	9		nC	$V_R = 600 \text{ V, } I_F = 4A$ $di/dt = 500 \text{ A/}\mu\text{s}$ $T_J = 25^{\circ}\text{C}$	
С	Total Capacitance	220 26 20		pF	$V_R = 0 \text{ V, } T_J = 25^{\circ}\text{C, } f = 1 \text{ MHz}$ $V_R = 200 \text{ V, } T_J = 25^{\circ}\text{C, } f = 1 \text{ MHz}$ $V_R = 400 \text{ V, } T_J = 25^{\circ}\text{C, } f = 1 \text{ MHz}$	

Note:

Thermal Characteristics

Symbol	Parameter	Тур.	Unit
$R_{_{\theta JC}}$	Thermal Resistance from Junction to Case	2.4	°C/W

Typical Performance

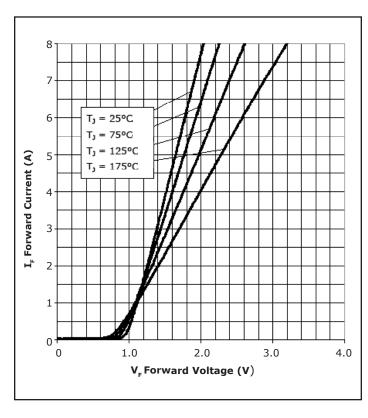


Figure 1. Forward Characteristics

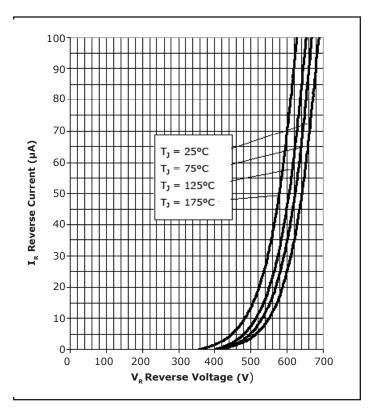
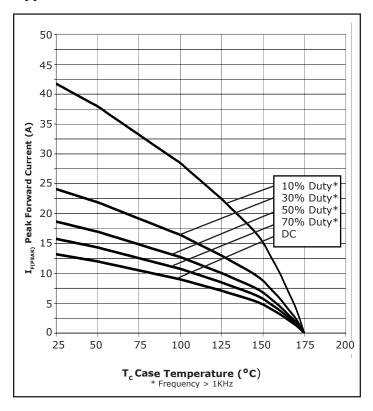


Figure 2. Reverse Characteristics

^{1.} This is a majority carrier diode, so there is no reverse recovery charge.



Typical Performance





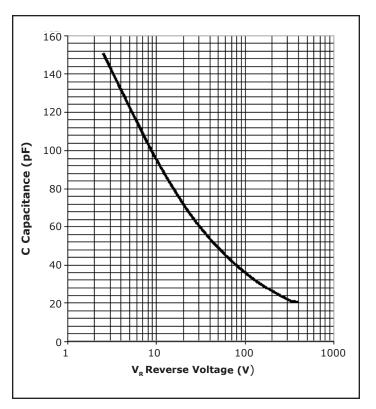


Figure 4. Capacitance vs. Reverse Voltage

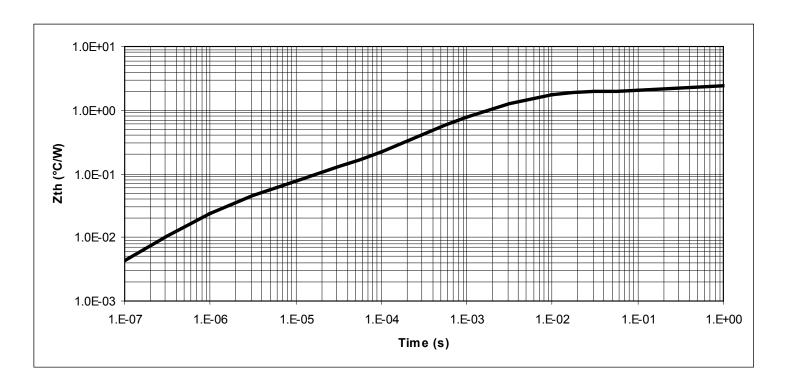


Figure 5. Transient Thermal Impedance



Typical Performance

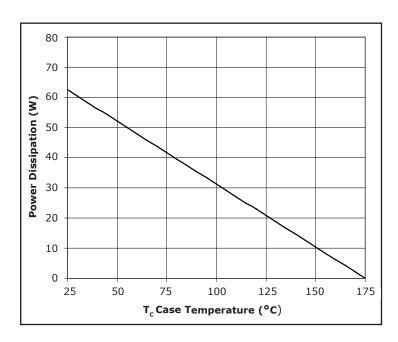
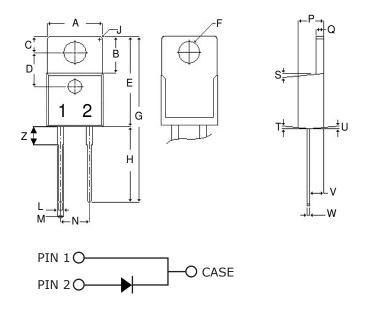


Figure 6. Power Derating



Package Dimensions

Package TO-220-2





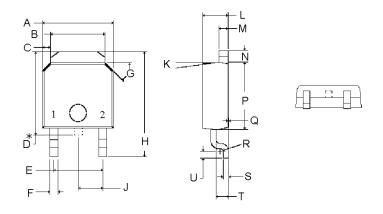
POS	Inc	hes	Millimeters		
PUS	Min	Max	Min	Max	
А	.381	.410	9.677	10.414	
В	.235	.255	5.969	6.477	
С	.100	.120	2.540	3.048	
D	.223	.337	5.664	8.560	
Е	.590	.615	14.986	15.621	
F	.143	.153	3.632	3.886	
G	1.105	1.147	28.067	29.134	
Н	.500	.550	12.700	13.970	
J	R 0.	197	R 0.197		
L	.025	.036	.635	.914	
М	.045	.055	1.143	1.397	
N	.195	.205	4.953	5.207	
Р	.165	.185	4.191	4.699	
Q	.048	.054	1.219	1.372	
S	3°	6°	3°	6°	
Т	3°	6°	3°	6°	
U	3°	6°	3°	6°	
V	.094	.110	2.388	2.794	
W	.014	.025	.356	.635	
Х	3°	5.5°	3°	5.5°	
Y	.385	.410	9.779	10.414	
z	.130	.150	3.302	3.810	

NOTE:

 Dimension L, M, W apply for Solder Dip Finish

Package Dimensions

Package TO-252-2





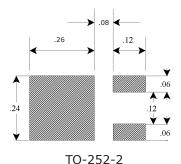
POS	Inc	hes	Millimeters		
P05	Min	Max	Min	Max	
А	.255	.265	6.477	6.731	
В	.197	.205	5.004	5.207	
С	.027	.033	.686	.838	
D*	.270	.322	6.858	8.179	
Е	.178	.182	4.521	4.623	
F	.025	.035	.635	.889	
G	44°	46°	44°	46°	
Н	.382	.397	9.703	10.084	
J	.090	TYP	2.286 TYP		
K	6°	8°	6°	8°	
L	.086	.094	2.184	2.388	
М	.030	.034	.762	.864	
N	.040	.044	1.016	1.118	
Р	.235	.245	5.969	6.223	
Q	0.00	.004	0.00	.102	
R	R0.01 TYP		R0.31 TYP		
S	.017	.023	.428	.588	
Т	.040	.044	1.016	1.118	
U	.021	.027	.534	1.118	

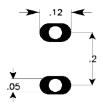
Note:

* Tab "D" may not be present



Recommended Solder Pad Layout





TO-220-2

Part Number	Package	Marking
CSD04060A	TO-220-2	CSD04060
CSD04060E	TO-252-2	CSD04060

Diode Model

$$\begin{array}{c|c} - & & \\ \hline - & & \\ - & & \\ \hline - & & \\ - & & \\ \hline - & & \\ - & & \\ \hline - & & \\ - & & \\ \hline - & & \\ - & & \\ \hline - & & \\ - & & \\ \hline - & & \\ - & & \\ \hline - & & \\ - & & \\ \hline - & & \\ - & & \\ \hline - & &$$

$$Vf_T = V_T + If*R_T$$

$$\begin{split} V_{T=}\,0.965 + & \left(T_j \, * \, \text{-} 1.3 \, * \, 10^{\text{-}3}\right) \\ R_{T=}\,0.096 + & \left(T_j \, * \, 1.06 \, * \, 10^{\text{-}3}\right) \end{split}$$

Note: T_i = Diode Junction Temperature In Degrees Celcius

"The levels of environmentally sensitive, persistent biologically toxic (PBT), persistent organic pollutants (POP), or otherwise restricted materials in this product are below the maximum concentration values (also referred to as the threshold limits) permitted for such substances, or are used in an exempted application, in accordance with EU Directive 2002/95/EC on the restriction of the use of certain hazardous substances in electrical and electronic equipment (RoHS), as amended through April 21, 2006. This part number was released previously with Sn/Pb solder plating as a standard industry finish. For more information please contact power_sales@cree.com "

This product has not been designed or tested for use in, and is not intended for use in, applications implanted into the human body nor in applications in which failure of the product could lead to death, personal injury or property damage, including but not limited to equipment used in the operation of nuclear facilities, life-support machines, cardiac defibrillators or similar emergency medical equipment, aircraft navigation or communication or control systems, air traffic control systems, or weapons systems.

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